

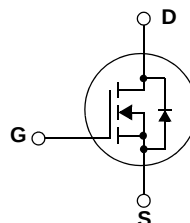
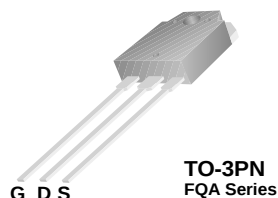
Features

- 9A, 900V, $R_{DS(on)} = 1.4\Omega @ V_{GS} = 10V$
- Low gate charge (typical 45 nC)
- Low C_{rss} (typical 14pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS compliant

Description

These N-Channel enhancement mode power field effect transistors are produced using Toohong proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies, active power factor correction, electronic lamp ballast based on half bridge topology.



Absolute Maximum Ratings

Symbol	Parameter	FQA9N90C_F109	Units
V_{DSS}	Drain-Source Voltage	900	V
I_D	Drain Current - Continuous ($T_C = 25^\circ C$)	9.0	A
	- Continuous ($T_C = 100^\circ C$)	5.7	A
I_{DM}	Drain Current - Pulsed (Note 1)	36	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	900	mJ
I_{AR}	Avalanche Current (Note 1)	9.0	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	28	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
P_D	Power Dissipation ($T_C = 25^\circ C$)	280	W
	- Derate above $25^\circ C$	2.22	W/ $^\circ C$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.45	$^\circ C/W$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24	--	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ C/W$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQA9N90C	FQA9N90C_F109	TO-3PN	--	--	30

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	900	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.99	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 900 V, V _{GS} = 0 V	--	--	10	μA
		V _{DS} = 720 V, T _C = 125°C	--	--	100	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0	--	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 4.5 A	--	1.12	1.4	Ω
g _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 4.5 A (Note 4)	--	9.2	--	S
Dynamic Characteristics						
C _{iSS}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	2100	2730	pF
C _{oSS}	Output Capacitance		--	175	230	pF
C _{rSS}	Reverse Transfer Capacitance		--	14	18	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 450 V, I _D = 11.0A, R _G = 25 Ω (Note 4, 5)	--	50	110	ns
t _r	Turn-On Rise Time		--	120	250	ns
t _{d(off)}	Turn-Off Delay Time		--	100	210	ns
t _f	Turn-Off Fall Time		--	75	160	ns
Q _g	Total Gate Charge	V _{DS} = 720 V, I _D = 11.0A, V _{GS} = 10 V (Note 4, 5)	--	45	58	nC
Q _{gs}	Gate-Source Charge		--	13	--	nC
Q _{gd}	Gate-Drain Charge		--	18	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	9.0	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	36	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S =9.0 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 9.0 A, dI _F / dt = 100 A/μs (Note 4)	--	550	--	ns
Q _{rr}	Reverse Recovery Charge		--	6.5	--	μC

NOTES:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 21mH, I_{AS} = 9.0A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 9.0A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

Typical Performance Characteristics

Figure 1. On-Region Characteristics

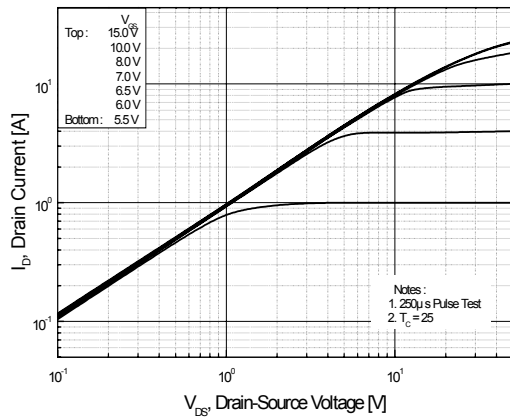


Figure 2. Transfer Characteristics

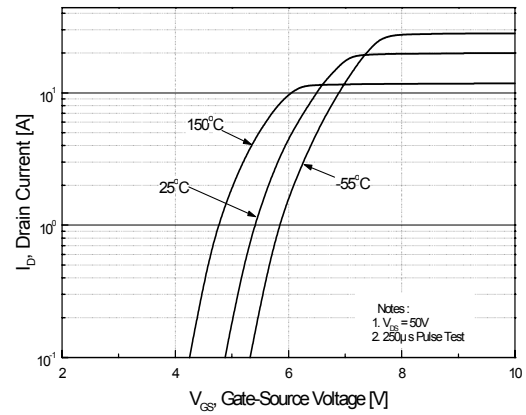


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

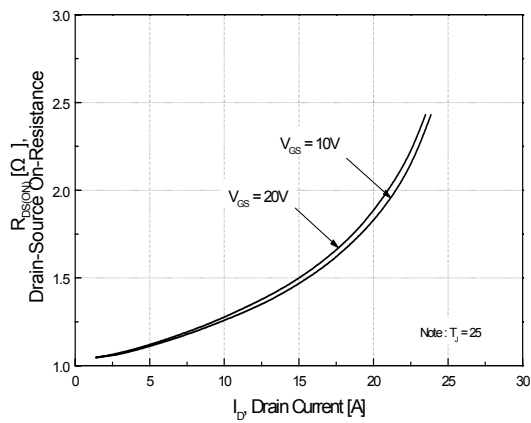


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

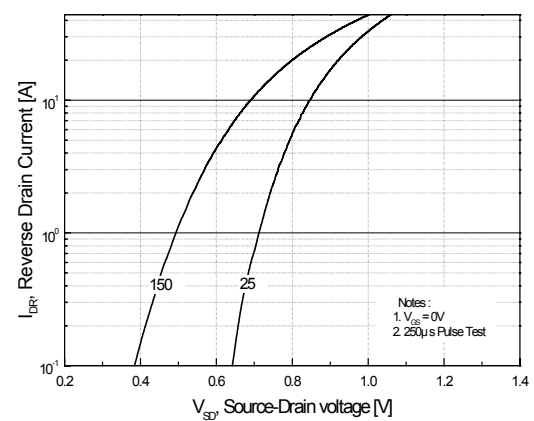


Figure 5. Capacitance Characteristics

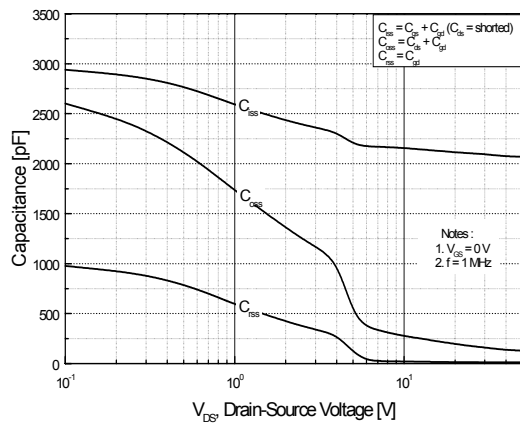
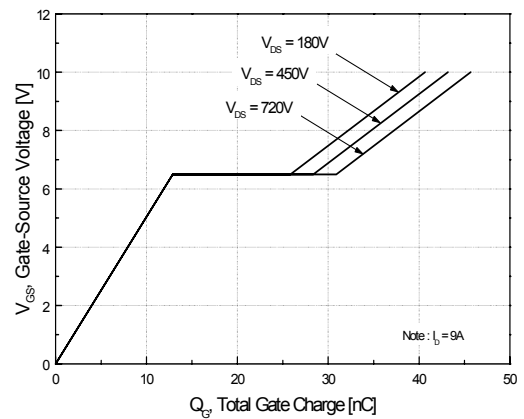


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

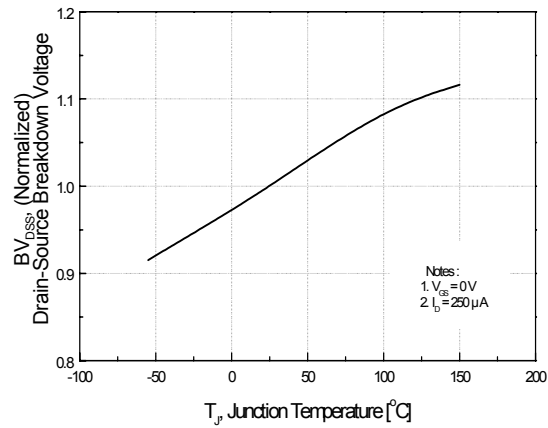


Figure 8. On-Resistance Variation vs. Temperature

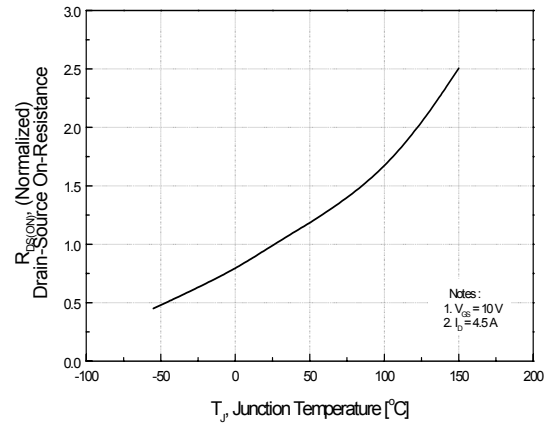


Figure 9. Maximum Safe Operating Area

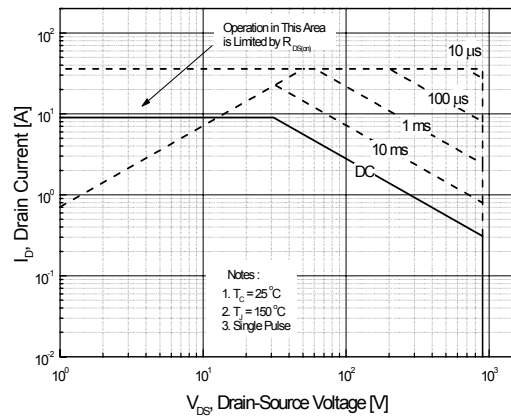


Figure 10. Maximum Drain Current vs. Case Temperature

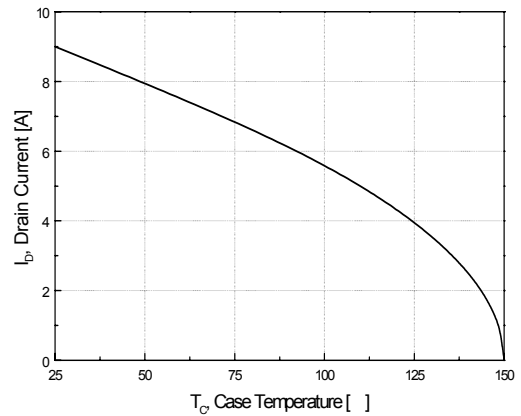


Figure 11. Transient Thermal Response Curve

